### Product / Process Change Notification



N° 2017-039-A

Dear Customer.

Please find attached our INFINEON Technologies PCN:

Introduction of additional wafer production site with 12" Wafer diameter for IGBT4 1200V (T4) and IGBT HighSpeed 3 (H3) technology. Furthermore 8" wafer diameter will be introduced for Diode EC4 1200V technology

Important information for your attention:

- Please respond to this PCN by indicating your decision on the approval form, sign it and return to your sales partner before 25. May 2017.
- Infineon aligns with the widely-recognized JEDEC STANDARD "JESD46", which stipulates: "Lack of acknowledgement of the PCN within 30 days constitutes acceptance of the change."

Your prompt reply will help Infineon Technologies to assure a smooth and well executed transition. If Infineon does not hear from your side by the due date, we will assume your full acceptance to this proposed change and its implementation.

Your attention and response to this matter is greatly appreciated.

Infineon Technologies AG
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Chairman of the Supervisory Board: Wolfgang Mayrhuber
Management Board: Dr. Reinhard Ploss (CEO), Dominik Asam, Dr. Helmut Gassel, Jochen Hanebeck
Registered Office: Neubiberg Commercial Register
Amtsgericht München HRB 126492

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## Product / Process Change Notification



#### N° 2017-039-A

► Products affected: Sales Name SP N° OPN Package

1200V IGBT4 Modules

Please refer to attached affected product list 1\_cip17039a

#### Detailed Change Information:

**Subject:** Introduction of additional wafer production site with

- 12" inch (300mm) wafer diameter capability for IGBT Chips and
- 8" inch (200mm) wafer diameter for Diode products.

**Reason:** Capacity extension and increasing security of supply 1200V IGBT4, IGBT HighSpeed 3 and Diode

<u>For IGBT products</u> 12" wafer manufacturing technology is meanwhile the established technology at IFX

<u>For Diodes</u> the 8" wafer manufacturing technology is, State of the Art' wafer manufacturing technology at Infineon. Therefore, the above mentioned products will be shifted from 6" inch wafer diameter to 8" inch wafer diameter.

#### Description: Old New IGBT ■ IGBT 8" inch: 8" inch: - Front end Villach/ Austria - Front end Villach, Austria - Front end Kulim/ Malaysia - Front end Kulim/ Malaysia - Front end Dresden/ Germany → Target production site front end Dresden/ Germany 12" inch Diode Diode 6" inch: 6" inch - Front end Villach/ Austria - Front end Villach/ Austria 8" inch: - Front end Villach/ Austria → Target production site front end Villach/ Austria 8" inch

► Product Identification: Individual module material number.

See attached list of affected products 1\_cip17039a

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▶ Impact of Change: No impact on electrical performance. Quality and reliability verified by

qualification. There is no change in form, fit and function There is no change in the assembly process at Infineon.

► Attachment: Affected product list 1\_cip17039a

#### ► Time Schedule:

Final qualification report: On request

First samples available: On request

Intended start of delivery: 01-Sept-2017 or directly after customer approval

If you have any questions, please do not hesitate to contact your local Sales office.

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